

# 54F/74F86 2-Input Exclusive-OR Gate

## **General Description**

This device contains four independent gates, each of which performs the logic exclusive-OR function.

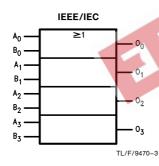
Commercial	Military	Package Number	Package Description			
74F86PC		N14A	14-Lead (0.300" Wide) Molded Dual-in-Line			
	54F86DM (Note 2)	J14A	14-Lead Ceramic Dual-in-Line			
74F86SC (Note 1)		M14A	14-Lead (0.150" Wide) Molded Small Outline, JEDEC			
74F86SJ (Note 1)		M14D	14-Lead (0.300" Wide) Molded Small Outline, EIAJ			
	54F86FM (Note 2)	W14B	14-Lead Cerpack			
	54F86LM (Note 2)	E20A	20-Lead Ceramic Leadless Chip Carrier, Type C			

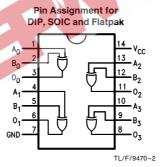
Note 1: Devices also available in 13" reel. Use suffix = SCX and SJX.

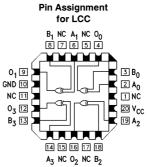
Note 2: Military grade device with environmental and burn-in processing. Use suffix = DMQB, FMQB and LMQB.

# **Logic Symbol**

# **Connection Diagrams**







TL/F/9470-1

#### **Unit Loading/Fan Out**

		54F/74F				
Pin Names	Description	U.L. HIGH/LOW	Input I <sub>IH</sub> /I <sub>IL</sub> Output I <sub>OH</sub> /I <sub>OL</sub>			
A <sub>n</sub> , B <sub>n</sub> O <sub>n</sub>	Inputs Outputs	1.0/1.0 50/33.3	20 μA/ - 0.6 mA - 1 mA/20 mA			

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#### Absolute Maximum Ratings (Note 1)

If Military/Aerospace specified devices are required, please contact the National Semiconductor Sales Office/Distributors for availability and specifications.

Storage Temperature -65°C to +150°C Ambient Temperature under Bias  $-55^{\circ}\text{C}$  to  $+125^{\circ}\text{C}$ -55°C to +175°C Junction Temperature under Bias  $-55^{\circ}$ C to  $+150^{\circ}$ C Plastic

V<sub>CC</sub> Pin Potential to Ground Pin -0.5V to +7.0VInput Voltage (Note 2) -0.5V to +7.0VInput Current (Note 2)  $-30\ \text{mA}$  to  $+5.0\ \text{mA}$ 

Voltage Applied to Output in HIGH State (with V<sub>CC</sub> = 0V)

 $-0.5 \mbox{V to V}_{CC} \\ -0.5 \mbox{V to } +5.5 \mbox{V}$ Standard Output TRI-STATE® Output

Current Applied to Output

in LOW State (Max) twice the rated  $I_{OL}$  (mA)

Note 1: Absolute maximum ratings are values beyond which the device may be damaged or have its useful life impaired. Functional operation under these conditions is not implied.

Note 2: Either voltage limit or current limit is sufficient to protect inputs.

#### **Recommended Operating Conditions**

Free Air Ambient Temperature

Military -55°C to +125°C Commercial  $0^{\circ}C$  to  $\,+\,70^{\circ}C$ 

Supply Voltage

 $+\,4.5V$  to  $+\,5.5V$ Military Commercial +4.5V to +5.5V

#### **DC Electrical Characteristics**

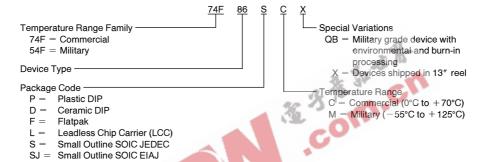
DC EI	ectrical Chara	cteristics					4	A R	
Symbol	ol Parameter		54F/74F			Units	v <sub>cc</sub>	Conditions	
Oymbor			Min Typ Max		Max	an a	100	Conditions	
$V_{IH}$	Input HIGH Voltage		2.0			V		Recognized as a HIGH Signal	
$V_{IL}$	Input LOW Voltage				0.8	V		Recognized as a LOW Signal	
$V_{CD}$	Input Clamp Diode Voltage			4	-1.2	V	Min	$I_{\text{IN}} = -18 \text{ mA}$	
V <sub>OH</sub>	Output HIGH Voltage	54F 10% V <sub>CC</sub> 74F 10% V <sub>CC</sub> 74F 5% V <sub>CC</sub>	2.5 2.5 2.7			V	Min	$I_{OH} = -1 \text{ mA}$ $I_{OH} = -1 \text{ mA}$ $I_{OH} = -1 \text{ mA}$	
V <sub>OL</sub>	Output LOW Voltage	54F 10% V <sub>CC</sub> 74F 10% V <sub>CC</sub>			0.5 0.5	V	Min	$I_{OL} = 20 \text{ mA}$ $I_{OL} = 20 \text{ mA}$	
I <sub>IH</sub>	Input HIGH Current	54F 74F			20.0 5.0	μΑ	Max	V <sub>IN</sub> = 2.7V	
I <sub>BVI</sub>	Input HIGH Current Breakdown Test	54F 74F			100 7.0	μΑ	Max	V <sub>IN</sub> = 7.0V	
I <sub>CEX</sub>	Output HIGH Leakage Current	54F 74F			250 50	μΑ	Max	$V_{OUT} = V_{CC}$	
V <sub>ID</sub>	Input Leakage Test	74F	4.75			V	0.0	$I_{\text{ID}} = 1.9  \mu\text{A}$ All other pins grounded	
I <sub>OD</sub>	Output Leakage Circuit Current	74F			3.75	μΑ	0.0	V <sub>IOD</sub> = 150 mV All other pins grounded	
I <sub>IL</sub>	Input LOW Current				-0.6	mA	Max	V <sub>IN</sub> = 0.5V	
los	Output Short-Circuit (	-60		-150	mA	Max	V <sub>OUT</sub> = 0V		
ICCH	Power Supply Curren		12	18	mA	Max	V <sub>O</sub> = HIGH		
I <sub>CCL</sub>	Power Supply Current			18	28	mA	Max	V <sub>O</sub> = LOW	

#### **AC Electrical Characteristics**

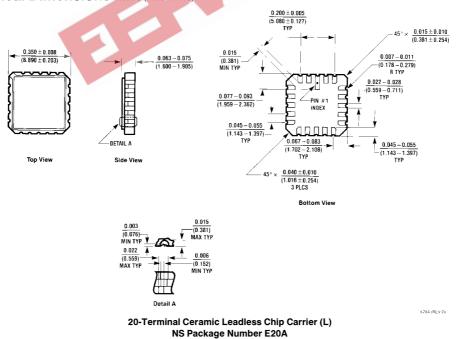
	Parameter	$ \begin{array}{c} {\it T_A = +25^{\circ}C} \\ {\it V_{CC} = +5.0V} \\ {\it C_L = 50pF} \end{array} $			5	4F	74F		
Symbol					$ extsf{T}_{ extsf{A}},  extsf{V}_{ extsf{CC}} =  extsf{Mil} \  extsf{C}_{ extsf{L}} =  extsf{50 pF}$		T <sub>A</sub> , V <sub>CC</sub> = Com C <sub>L</sub> = 50 pF		Units
		Min	Тур	Max	Min	Max	Min	Max	
t <sub>PLH</sub> t <sub>PHL</sub>	Propagation Delay  A <sub>n</sub> , B <sub>n</sub> to O <sub>n</sub> (Other Input LOW)	3.0 3.0	4.0 4.2	5.5 5.5	2.5 3.0	7.0 7.0	3.0 3.0	6.5 6.5	ns
t <sub>PLH</sub> t <sub>PHL</sub>	Propagation Delay A <sub>n</sub> , B <sub>n</sub> to O <sub>n</sub> (Other Input HIGH)	3.5 3.0	5.3 4.7	7.0 6.5	3.5 3.0	8.5 8.0	3.5 3.0	8.0 7.5	ns

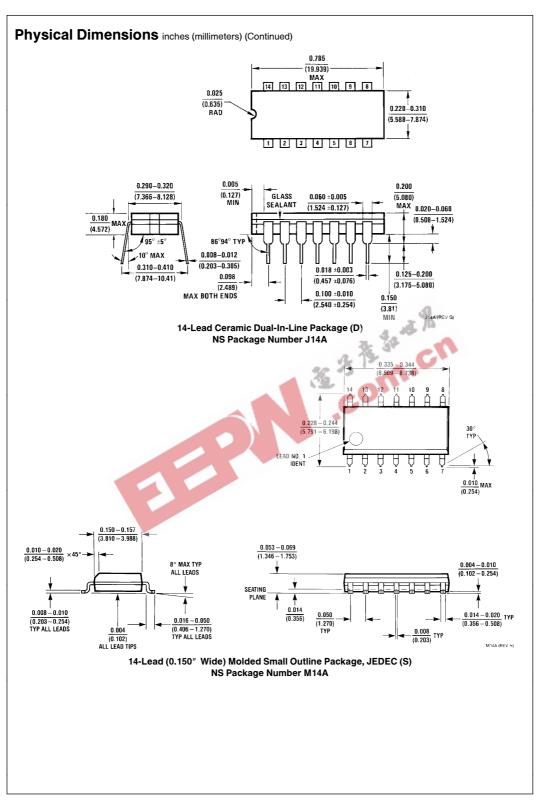
# **Ordering Information**

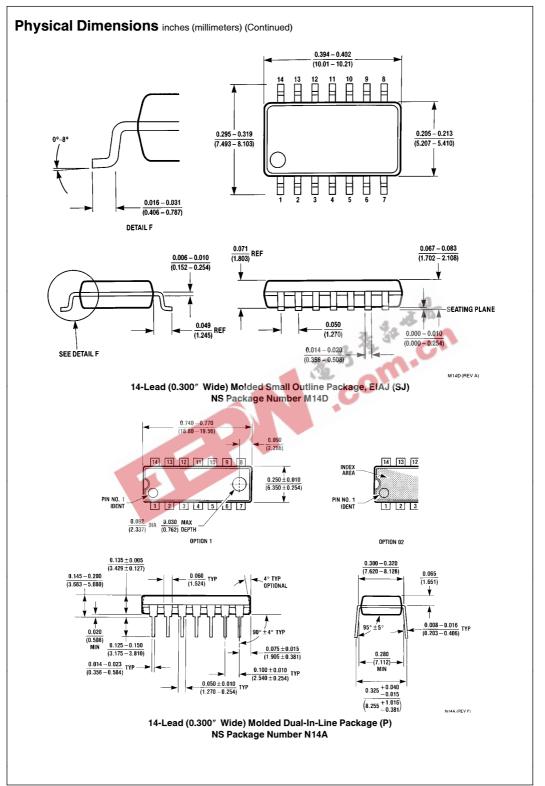
The device number is used to form part of a simplified purchasing code where the package type and temperature range are defined as follows:

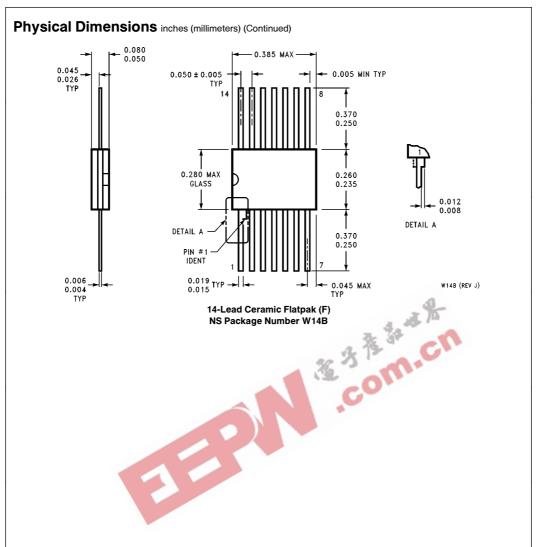


### Physical Dimensions inches (millimeters)









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